

IN THE CLAIMS

Please enter the following amendments. The amendments are fully supported in the specification and no new material is added.

- C1
1. (Twice Amended) A low impedance band-gap reference circuit, comprising:
 - a band-gap reference circuit;
 - a buffer circuit electronically coupled with said band-gap reference circuit; and
 - a voltage pull-up device electronically coupled ~~with~~ between said band-gap reference circuit and said buffer circuit, wherein said voltage pull-up device acts to reduce a required supply voltage to maintain a band-gap reference voltage and wherein said voltage pull-up device is implemented as a transistor with a VBE of less than 1.0 volts ~~VBE~~.
 2. (Amended) A low impedance band-gap reference circuit as described in Claim 1, wherein said band-gap reference circuit resides in an integrated circuit device.
 3. (Amended) A low impedance band-gap reference circuit as described in Claim 1, wherein said band-gap reference circuit is implemented in a silicon substrate.
 4. (Amended) A low impedance band-gap reference circuit as described in Claim 1, wherein said buffer circuit is implemented as a transistor.
 5. (Previously Cancelled)
 6. (Twice Amended) A low impedance band-gap reference circuit as described in Claim 1, wherein said band gap reference voltage is provided by current through a transistor with a VBE of less than 1.0 volts.
 7. (Twice Amended) An electronic device, comprising:
 - a silicon substrate;
 - electronic circuitry constructed in said silicon substrate; and
 - a low impedance band-gap reference circuit electronically coupled in said electronic device, wherein said electronic circuitry requires reference to the output voltage of said band-gap reference circuit and said band-gap reference circuit is enabled for low

impedance by a buffer circuit comprising a transistor with a VBE of less than 1.0 volts
VBE.

8. An electronic device as described in Claim 7, wherein said electronic device is an integrated circuit device.

9. (Previously Cancelled)

10. (Previously Cancelled)

11. (Previously Amended) An electronic device as described in Claim 7, wherein said transistor with less than 1.0 VBE is connected as an emitter follower.

12. An electronic device as described in Claim 7, wherein said band-gap reference circuit is enabled for low supply voltage.

13. An electronic device as described in Claim 12, wherein said band-gap reference circuit is enabled for said low supply voltage by a voltage pull-up device.

14. (Previously Cancelled)

15. (Previously Amended) An electronic device as described in Claim 13, wherein said band gap reference voltage is provided by current through a transistor with a VBE of less than 1.0 volts.

16. (Twice Amended) In an electronic device, a method for providing a reference voltage, comprising:

flowing current through an electronic element such that the band-gap voltage of said electronic element provides said reference voltage;

providing a buffer circuit enabled to provide low impedance; and

adjusting the voltage across said buffer circuit so that said band-gap reference voltage is maintained, wherein said voltage is a VBE of less than 1.0 V volts.

17. (Original) A method as described in Claim 16, wherein said electronic device is an integrated circuit device.

18. (Original) A method as described in Claim 16, wherein said buffer circuit is implemented as a transistor circuit.

19. (Original) A method as described in Claim 18, wherein said transistor circuit is connected as an emitter follower.

C' 20. (Original) A method as described in Claim 16, wherein said band-gap reference circuit is enabled for low supply voltage.

21. (Original) A method as described in Claim 20, wherein said band-gap reference circuit is enabled for said low supply voltage by a voltage pull-up device.

22. (Previously Cancelled)

23. (Previously Amended) A method as described in Claim 21, wherein said band gap reference voltage is provided by current through a transistor with a VBE of less than 1.0 volts.
